Vishay Semiconductors

High Voltage Phase Control Thyristor, 12 A



www.vishay.com

3L TO-220AB

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PRIMARY CHARACTERISTICS					
I _{T(AV)} 8 A					
V _{DRM} /V _{RRM}	800 V				
V _{TM}	1.2 V				
I _{GT}	15 mA				
TJ	-40 °C to 125 °C				
Package	3L TO-220AB				
Circuit configuration	Single SCR				

FEATURES

- Designed and qualified according to JEDEC[®]-JESD 47
- 125 °C max. operating junction temperature
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

• Typical usage is in input rectification crowbar (soft start) and AC switch in motor control, UPS, welding, and battery charge.

DESCRIPTION

The VS-12TTS08... high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C, common heatsink of 1 °C/W	13.5	17	A		

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
I _{T(AV)}	Sinusoidal waveform	8	٨		
I _{T(RMS)}		12.5	A		
V _{DRM} /V _{RRM}		800	V		
I _{TSM}		110	А		
V _T	8 A, T _J = 25 °C	1.2	V		
dV/dt		150	V/µs		
dl/dt		100	A/µs		
TJ	Range	-40 to +125	°C		

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK VOLTAGE V	V _{DRM} , MAXIMUM PEAK DIRECT VOLTAGE V	I _{RRM} ∕I _{DRM} AT 125 °C mA			
VS-12TTS08-M3	800	800	1.0			



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VS-12TTS08-M3

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ABSOLUTE MAXIMUM RATING	S				
PARAMETER	SYMBOL		TEST CONDITIONS		UNITS
Maximum average on-state current	I _{T(AV)}	T _ 109 °C	180° conduction, half sine wave	8	А
Maximum RMS on-state current	I _{T(RMS)}	1 _C = 106 C,	Too conduction, han sine wave	12.5	
Maximum peak, one-cycle,	I =0.1	10 ms sine p	ulse, rated V_{RRM} applied, T_J = 125 °C	95	A
non-repetitive surge current	I _{TSM}	10 ms sine p	ulse, no voltage reapplied, $T_J = 125 \ ^{\circ}C$	110	
Maximum I ² t for fusing	l ² t	10 ms sine p	ulse, rated V_{RRM} applied, $T_J = 125 \ ^\circ C$	45	A ² s
Maximum Ft for fusing	1-1	10 ms sine p	10 ms sine pulse, no voltage reapplied, T_J = 125 °C		A-S
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 7	10 ms, no voltage reapplied, $T_J = 125 \ ^\circ C$	640	A²√s
Maximum on-state voltage drop	V _{TM}	8 A, T _J = 25 °	8 A, T _J = 25 °C		V
On-state slope resistance	r _t	T _{.1} = 125 °C	T 105 %		mΩ
Threshold voltage	V _{T(TO)}	1j=125 0		0.87	V
Maximum reverse and direct leakage	1/1	T _J = 25 °C		0.05	
current	I _{RM} /I _{DM}	T _J = 125 °C	$V_{R} = Rated V_{RRM}/V_{DRM}$	1.0	
Typical holding current	Ι _Η	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		30	mA
Maximum latching current	١L	Anode supply = 6 V, resistive load, T_J = 25 °C		50	
Maximum rate of rise of off-state voltage	dV/dt	$T_J = T_J max.$, linear to 80 °C, $V_{DRM} = R_g - k = Open$		150	V/µs
Maximum rate of rise of turned-on current	dl/dt			100	A/µs

TRIGGERING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum peak gate power	P _{GM}		8.0	W		
Maximum average gate power	P _{G(AV)}		2.0	vv		
Maximum peak positive gate current	+ I _{GM}		1.5	А		
Maximum peak negative gate voltage	- V _{GM}		10	V		
	I _{GT}	Anode supply = 6 V, resistive load, T_J = - 65 °C	20			
Maximum required DC gate current to trigger		Anode supply = 6 V, resistive load, $T_J = 25 \text{ °C}$	15	mA		
		Anode supply = 6 V, resistive load, T_J = 125 °C	10			
		Anode supply = 6 V, resistive load, T_J = - 65 °C	1.2			
Maximum required DC gate voltage to trigger	V _{GT}	Anode supply = 6 V, resistive load, T_J = 25 °C	1	V		
		Anode supply = 6 V, resistive load, T_J = 125 °C	0.7	v		
Maximum DC gate voltage not to trigger	V _{GD}	T 105 °C V Detectivelye	0.2			
Maximum DC gate current not to trigger	I _{GD}	T _J = 125 °C, V _{DRM} = Rated value	0.1	mA		

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Typical turn-on time	t _{gt}	T _J = 25 °C	0.8			
Typical reverse recovery time	t _{rr}	T. = 125 °C	3	μs		
Typical turn-off time	tq	1J = 125 C	100			

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VS-12TTS08-M3

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THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range		T _J , T _{Stg}		-40 to 125	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	1.5	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	oz.
Mounting torque	minimum			6 (5)	kgf ⋅ cm
Mounting torque	maximum			12 (10)	(lbf · in)
Marking device			Case style 3L TO-220AB	12TTS08	

Maximum Average On-State Power Loss (W)

Maximum Average On-State Power Loss (W)

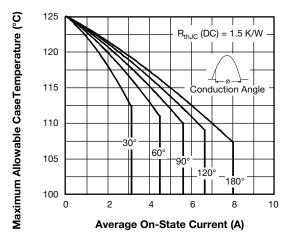


Fig. 1 - Current Ratings Characteristics

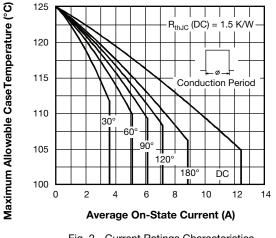


Fig. 2 - Current Ratings Characteristics

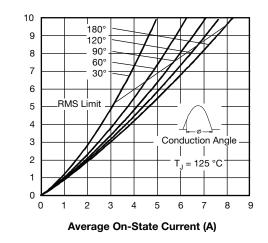


Fig. 3 - On-State Power Loss Characteristics

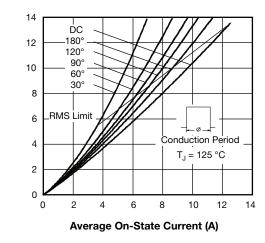


Fig. 4 - On-State Power Loss Characteristics

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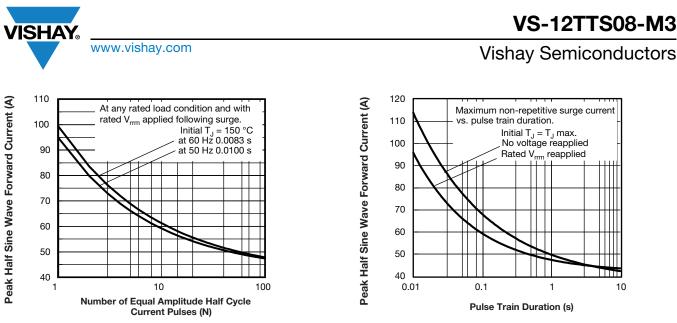


Fig. 5 - Maximum Non-Repetitive Surge Current



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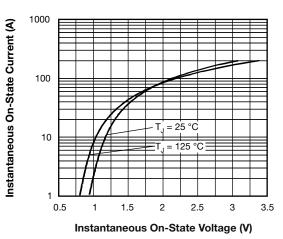


Fig. 7 - On-State Voltage Drop Characteristics

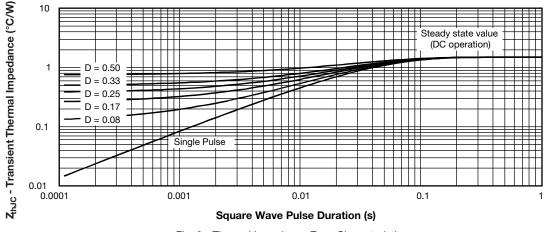


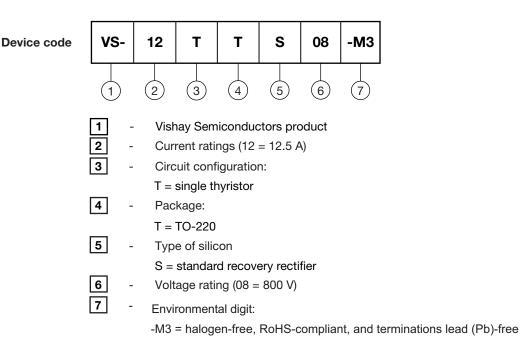
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE



ORDERING INFORMATION (Example)						
PREFERRED P/N QUANTITY PER T/R MINIMUM ORDER QUANTITY PACKAGING DESCRIPTION						
VS-12TTS08-M3	50	1000	Antistatic plastic tubes			

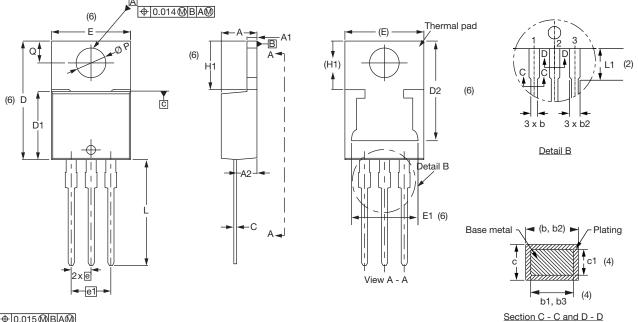
LINKS TO RELATED DOCUMENTS				
Dimensions <u>www.vishay.com/doc?96154</u>				
Part marking information www.vishay.com/doc?95028				



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3L TO-220AB

DIMENSIONS in millimeters and inches



⊕0.015@BA@





SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STWIDOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.50	2.92	0.098	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.35	0.585	0.604	3
D1	8.38	9.02	0.330	0.355	

Conforms to JEDEC [®]	outline	TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
D2	11.68	13.30	0.460	0.524	6, 7
Е	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.91	0.139	0.154	
Q	2.60	3.00	0.102	0.118	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

⁽⁴⁾ Dimension b1, b3, and c1 apply to base metal only

(5) Controlling dimensions: inches

⁽⁶⁾ Thermal pad contour optional within dimensions E, H1, D2, and E1

⁽⁷⁾ Outline conforms to JEDEC[®] TO-220, except D2

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